

Silicon NPN Power Transistors

2N6262

DESCRIPTION

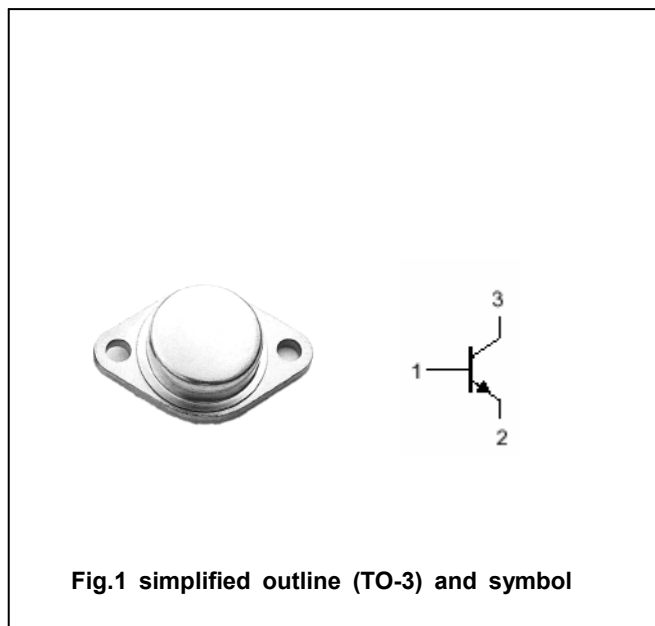
- With TO-3 package
- Low collector saturation voltage
- Excellent safe operating area

APPLICATIONS

- Designed for audio amplifier and switching circuits applications

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	170	V
V_{CEO}	Collector-emitter voltage	Open base	150	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		10	A
P_D	Total Power Dissipation	$T_C = 25 \square$	150	W
T_j	Junction temperature		150	\square
T_{stg}	Storage temperature		-65~200	\square

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance junction to case	1.17	\square/W

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO(SUS)}	Collector-emitter sustaining voltage	I _C =0.2A ; I _B =0	150			V
V _{CEsat}	Collector-emitter saturation voltage	I _C =5A ; I _B =0.5A			2.0	V
V _{BEsat}	Base-emitter saturation voltage	I _C =10A ; I _B =2A			3.5	V
V _{BE}	Base-emitter on voltage	I _C =3A ; V _{CE} =2V			1.8	V
I _{CEO}	Collector cut-off current	V _{CE} =100V; I _B =0			1.0	mA
I _{CEV}	Collector cut-off current	V _{CE} =150V; V _{BE(off)} =1.5V T _C =150°C			0.1 5.0	mA
I _{CBO}	Emitter cut-off current	V _{CB} =150V; I _E =0			0.1	mA
I _{EBO}	Emitter cut-off current	V _{EB} =5V; I _C =0			0.1	mA
h _{FE}	DC current gain	I _C =3A ; V _{CE} =2V	20		70	
f _T	Transition frequency	I _C =1A; V _{CE} =10V	0.8			MHz

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PACKAGE OUTLINE



Fig.2 outline dimensions (unindicated tolerance:±0.10mm)